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What is claimed is:

1. An apparatus for processing a process region of a substrate; using a plasma, comprising:
 - a container substantially formed of a conductive material;
 - a partition plate dividing said container into an air-tight process chamber and an air-tight auxiliary chamber, and having a window plate made of dielectric;
 - a main pump exhaust for exhausting and setting said process chamber to a vacuum;
 - a work table arranged in said process chamber and having a support face facing said window plate, said substrate being mounted on said support face, with said process region facing said window plate;
 - a main supply for supplying a process gas between said window plate and said substrate mounted on said support face, at least part of said process gas being transformed into said plasma;
 - an induction electrode, for generating electromagnetic field between (1) said window plate and (2) said substrate mounted on said support face, to induce generation of said plasma, and including a coil arranged in said auxiliary chamber and facing said window plate;
 - a power supply section for applying a high frequency voltage to said coil;
 - an auxiliary exhaust pump for exhausting and setting said auxiliary chamber to a vacuum; and
 - a pressure controller connected to said auxiliary exhaust pump for keeping a pressure difference between pressures in said process and auxiliary chambers at a minimum value.
2. The apparatus according to claim 1, further comprising grounding means for grounding said container.
3. The apparatus according to claim 1, wherein said pressure controller is connected to said main exhaust pump.
4. The apparatus according to claim 1, further comprising a cooler for cooling said coil.
5. The apparatus according to claim 1, further comprising an auxiliary supply for supplying an inactive gas into said auxiliary chamber.
6. The apparatus according to claim 5, wherein said inactive gas supplied into said auxiliary chamber is a coolant, by which said coil is cooled.
7. The apparatus according to claim 6, wherein said auxiliary supply comprises a shower head arranged above said coil and having a plurality of gas supply holes facing said coil.
8. The apparatus according to claim 1, further comprising a seat arranged on said window plate and supporting said coil.]

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9. (Previously Amended) [The] An apparatus [according to claim 8] for processing a process region of a substrate using a plasma comprising:
a container substantially formed of a conductive material;
a partition plate dividing said container into an air-tight process chamber and an air-tight auxiliary chamber, and having a window plate made of dielectric;
a main exhaust pump for exhausting and setting said process chamber to a vacuum;
a work table arranged in said process chamber and having a support face facing said window plate, said substrate being mounted on said support face, with said process region facing said window plate;
a main supply for supplying a process gas between said window plate and said substrate mounted on said support face, at least part of said process gas being transformed into said plasma;
an induction electrode, for generating electromagnetic field between (1) said window plate and (2) said substrate mounted on said support face, to induce generation of said plasma, and including a coil arranged in said auxiliary chamber and facing said window plate;
a power supply section for applying a high frequency voltage to said coil;
an auxiliary exhaust pump for exhausting and setting said auxiliary chamber to a vacuum;
a pressure controller connected to said auxiliary exhaust pump for keeping a pressure difference between pressures in said process and auxiliary chambers at a minimum value; and
a seat arranged on said window plate and supporting said coil;
wherein a passage through which coolant is circulated is formed in said seat.

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10. The apparatus according to claim 1, further comprising a lower electrode arranged in said work table and a power supply for applying a high frequency potential to said lower electrode.

11. The apparatus according to claim 10, wherein said apparatus is a plasma CVD apparatus to form a film on said process region of said substrate, said process gas is decomposed to provide a material of said film.

12. The apparatus according to claim 11, wherein said process gas comprises first and second gases, and said main supply comprises first and second supply members respec-

tively supplying said first and second gases, and wherein said second gas is transformed into said plasma while said first gas is excited and decomposed by said plasma.

13. The apparatus according to claim 12, wherein said first supply member includes a supply port arranged between said window plate and said support face, and said second supply member includes a supply port arranged between said window plate and said supply port of said first supply member.

14. The apparatus according to claim 13, wherein said first supply member comprises a first supply head arranged between said window plate and said support face and made of dielectric, and said supply port of said first supply member comprises a plurality of supply holes formed on said first supply member and arranged to uniformly cover the whole of said process region of said substrate mounted on said support face.

15. The apparatus according to claim 14, wherein said first supply head comprises a lattice formed of a combination of pipe elements through which said first gas flows.

16. The apparatus according to claim 15, wherein said second supply member comprises a second supply head arranged between said window plate and said first supply head, made of dielectric, and comprising continuous frame formed of a combination of pipe elements through which said second gas flows, and said supply port of said second supply member comprises a plurality of supply holes formed on said second supply member.

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25. (Previously Amended) An apparatus for processing a process region of a substrate, using a plasma, comprising:
a container substantially formed of a conductive material;
a partition plate supported by said container and defining an air-tight process container portion and an air-tight auxiliary portion, and having a window plate made of dielectric;
a main exhaust pump for exhausting and setting said process container portion to a vacuum;
a work table arranged in said process container portion and having a support face facing said window plate, the substrate being mountable on said support face with the process region facing said window plate;
a main supply for supplying a process gas between said window plate and the substrate mounted on said support face, at least part of the process gas being transformable into the plasma;

a planar spiral coil for generating an electromagnetic field between said window plate and the substrate mounted on said support face to induce generation of the plasma, arranged in said auxiliary container portion and facing said window plate;

a power supply section for applying a high frequency voltage to said planar spiral coil;

an auxiliary exhaust pump for exhausting and setting said auxiliary container portion to a vacuum;

a pressure controller connected to said auxiliary exhaust pump for keeping a pressure difference between pressures in said process and auxiliary container portions at a minimum value; and

a seat arranged in window plate and supporting said planar spiral coil;

wherein a passage through which coolant is circulated is formed in said seat.

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37. (Previously Amended) An apparatus for processing with a plasma a process region of a substrate, comprising:

a container;

a dielectric window supported by said container and defining a first container portion and a second container portion separated by said dielectric window;

a table for supporting the substrate in said first container portion to face said window;

a first exhaust means connected to said first container portion for drawing a vacuum in said first container portion;

a first supply for supplying a process gas to said first container portion;
a planar spiral coil for generating an electromagnetic field between said window and the substrate supported on said table to induce generation of the plasma, said planar spiral coil being provided in said second container portion proximate said window;

a power supply for supplying a voltage to said coil;
a second exhaust means connected to said second container portion for drawing a vacuum in said second container portion; and
a second supply connected to said second container portion, comprising a gas supply pipe and a gas source for supplying an auxiliary gas to said second container portion;

wherein at least one of said first and second exhaust means are controllable to control a pressure differential across said window at a minimum value.

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38. (Previously Presented) The apparatus according to claim 37, further comprising a controller for controlling said first exhaust means to control the pressure differential.

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39. (Previously Presented) The apparatus according to claim 37, further comprising a controller for controlling the second exhaust means to control the pressure differential.

21 18
40. (Previously Amended) The apparatus according to claim 37, wherein said second exhaust means is controllable according to an amount of the auxiliary gas supplied by said second supply to control the pressure differential across said window at the minimum value.

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41. (Previously Presented) The apparatus according to claim 37, wherein said second exhaust means includes an exhaust pump controllable to control the pressure differential across said window at the minimum value.

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42. (Previously Presented) The apparatus according to claim 41, further comprising a controller for controlling said exhaust pump.

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43. (Previously Presented) The apparatus according to claim 37, further comprising a controller for controlling the second exhaust means according to the supply of the auxiliary gas through said second supply, to control the pressure differential across said window as the minimum value.

23 44. (Previously Presented) The apparatus according to claim 37, wherein said second exhaust means is controllable according to a pressure in said first container portion.

24 45. (Previously Presented) The apparatus according to claim 37, wherein said first exhaust means includes an exhaust pump.

25 46. (Previously Presented) The apparatus according to claim 45, further comprising a controller connected to said exhaust pump.

26 47. (Previously Presented) The apparatus according to claim 37, wherein said container is substantially formed of a conductive material.

27 48. (Previously Presented) The apparatus according to claim 37, wherein said dielectric window is supported on an inner surface of said container.

28 49. (Previously Presented) The apparatus according to claim 37, further comprising grounding means for grounding said container.

29 50. (Previously Amended) The apparatus according to claim 37, further comprising a cooler for cooling said planar spiral coil.

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51. (Previously Amended) The apparatus according to claim 37, wherein said auxiliary gas is a coolant by which said planar spiral coil is cooled.

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52. (Previously Amended) The apparatus according to claim 37, wherein said second supply comprises a shower head arranged above said planar spiral coil and having a plurality of gas supply holes facing said planar spiral coil.

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53. (Previously Amended) The apparatus according to claim 37, further comprising a seat arranged on said window and supporting said planar spiral coil.

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54. (Previously Presented) The apparatus according to claim 53, wherein a passage through which a coolant is circulated is formed on said seat.

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55. (Previously Presented) The apparatus according to claim 37, further comprising a lower electrode arranged in said work table and a power supply for applying a high frequency potential to said lower electrode.

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56. (Previously Presented) The apparatus according to claim 37, wherein said apparatus is a plasma CVD apparatus to form a film on the process region of the substrate, the process gas being decomposable to provide a material of the film.

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57. (Previously Presented) The apparatus according to claim 37, wherein the process gas comprises first and second gases, and the first supply comprises first and second supply members respectively for supplying the first and second gases, and wherein the second gas is transformable into the plasma when the first gas is excited and decomposed by said plasma.

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58. (Previously Presented) The apparatus according to claim 57, wherein said first supply member includes a supply port arranged between said window and said table, and said second supply member includes a supply port arranged between said window and said supply port of said first supply member.

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59. (Previously Amended) The apparatus according to claim 58, wherein said first supply member comprises a first supply head arranged between said window and said table and is made of dielectric, and said supply port of said first supply member comprises a plurality of supply holes formed on said first supply member and arranged to uniformly cover the whole of the process region of the substrate mounted on said table.

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60. (Previously Presented) The apparatus according to claim 59, wherein said first supply head comprises a lattice formed of a combination of pipe elements through which the first gas flows.

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61. (Previously Presented) The apparatus according to claim 60, wherein said second supply member comprises a second supply head arranged between said window and said first supply head, made of dielectric, and comprising a continuous frame formed of a combination of pipe elements through which the second gas flows, and said supply port of said second supply member comprises a plurality of supply holes formed on said second supply member.

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62. (Previously Presented) The apparatus according to claim 37, wherein the pressure differential across said window is controlled to be in a preselected range.

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63. (Previously Presented) The apparatus according to claim 37, wherein said dielectric window has a thickness in a preselected range.

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77. (Previously Amended) An apparatus for processing a substrate in a plasma comprising:
a container;
a dielectric window supported by said container and dividing said container into a first container portion and a second container portion;
first vacuum means for creating a first vacuum in said first container portion;

second vacuum means for creating a second vacuum in said second container portion;

a controller for controlling at least one of said first and second vacuum means in order to control a differential pressure across said window at a minimum value;

a table arranged in said first container portion for supporting the substrate;

a first supply for supplying a process gas to said first container portion;

an planar spiral coil arranged in said second container portion;

a voltage supply to said planar spiral coil for generating an electromagnetic field

whereby generation of the plasma is induced in said first container portion; and

a seat arranged in the said window and supporting said planar spiral coil;

wherein a passage through which coolant is circulated is formed in said seat.

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85. (Previously Amended) An apparatus for processing a process region of a substrate, using a plasma, comprising:

a container substantially formed of a conductive material;

a partition plate supported by said container and defining an air-tight process container portion and an air-tight auxiliary container portion, and having a window plate made of dielectric;

a work table arranged in said process container portion and having a support face facing said window plate, the substrate being mountable on said support face with the process region facing said window plate;

a main supply for supplying a process gas between said window plate and the substrate mounted on said support face, at least part of the process gas being transformable into the plasma;

a planar spiral coil having a quadrilateral outer configuration for generating an electromagnetic field between said window plate and the substrate mounted on said support face to induce generation of the plasma, arranged in said auxiliary container portion and facing said window plate;

a power supply section for applying a high frequency voltage to said antenna;

a pressure controller controlling a pressure difference between a pressure in said process container portion and a pressure in said auxiliary container portion lower than a predetermined value; and

a seat arranged on said window plate supporting said planar spiral coil, said seat having a passage therethrough for circulating a coolant.

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86. (Previously Presented) The apparatus according to claim 85, further comprising an exhaust pump connected to at least one of the container portions, wherein the pressure controller controls operation of said exhaust pump to control the pressure difference.

118 / 119
87. (Previously Presented) The apparatus according to claim 85, further comprising grounding means for grounding said container.

120 / 121
92. (Previously Presented) The apparatus according to claim 85, further comprising a lower electrode arranged in said work table and a power supply for applying a high frequency potential to said lower electrode.

122 / 123
93. (Previously Presented) The apparatus according to claim 92 wherein said apparatus is a plasma CVD apparatus to form a film on the process region of the substrate, the process gas being decomposable to provide a material of the film.

124 / 125
94. (Previously Presented) The apparatus according to claim 93, wherein the process gas comprises first and second gases, and the main supply comprises first and second supply members respectively for supplying the first and second gases, and wherein the second gas is transformable into the plasma when the first gas is excited and decomposed by said plasma.

126 / 127
95. (Previously Presented) The apparatus according to claim 94, wherein said first supply member includes a supply port arranged between said window plate

and said support face, and said second supply member includes a supply port arranged
between said window plate and said supply port of said first supply member.

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96. (Previously Presented) The apparatus according to claim 95, wherein
said first supply member comprises a first supply head arranged between said window
plate and said support face and made of dielectric, and said supply port of said first
supply member comprises a plurality of supply holes formed on said first supply
member and arranged to uniformly cover the whole of the process region of the
substrate mounted on said support face.

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97. (Previously Presented) The apparatus according to claim 96, wherein
said first supply head comprises a lattice formed of a combination of pipe elements
through which the first gas flows.

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98. (Previously Presented) The apparatus according to claim 97, wherein
said second supply member comprises a second supply head arranged between said
window plate and said first supply head, made of dielectric, and comprising a
continuous frame formed of a combination of pipe elements through which the second
gas flows, and said supply port of said second supply member comprises a plurality of
supply holes formed on said second supply member.

~~34~~ 99. (Previously Presented) The apparatus according to claim 85, wherein said partition plate is supported on an inner surface of said container.

~~55~~ 100. (Previously Amended) An apparatus for processing with a plasma a process region of a substrate, comprising:
a container;
a dielectric window supported by said container and defining a first container portion and a second container portion separated by said dielectric window, said first container portion and said second container portion each having substantially the same diameter;
a table for supporting the substrate in said first container portion to face said window;
a first supply for supplying a process gas to said first container portion;
a planar spiral coil for generating an electromagnetic field between said window and the substrate supported on said table to induce generation of the plasma, said planar spiral coil being provided in said second container portion proximate said window;
a power supply for supplying a voltage to said coil;
a second supply connected to said second container portion, comprising a gas source and a gas supply pipe for supplying an auxiliary gas to said second container portion;

wherein a pressure difference between a pressure in said first container portion and a pressure in said second container portion is controllable below a predetermined value to reduce a load caused by the pressure difference on said dielectric window.

59 / 58
101. (Previously Presented) The apparatus according to claim 100, further comprising a controller for controlling the pressure difference.

60 / 59
102. (Previously Presented) The apparatus according to claim 101, further comprising an exhaust pump connected to at least one container portion, wherein the controller controls operation of said pump.

61 / 58
103. (Previously Presented) The apparatus according to claim 100, wherein said container is substantially formed of a conductive material.

62 / 58
104. (Previously Presented) The apparatus according to claim 100, wherein said dielectric window is supported on an inner surface of said container.

63 / 58
105. (Previously Presented) The apparatus according to claim 100, further comprising grounding means for grounding said container.

64 / 58
106. (Previously Amended) The apparatus according to claim 100, further comprising a cooler for controlling a temperature of said planar spiral coil.

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107. (Previously Amended) The apparatus according to claim 100, further comprising a coolant flow passage including a coolant flow for cooling said planar spiral coil.

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108. (Previously Amended) The apparatus according to claim 100, further comprising a seat arranged on said window and supporting said planar spiral coil.

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109. (Previously Presented) The apparatus according to claim 108, wherein a passage through which a coolant is circulated is formed in said seat.

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110. (Previously Presented) The apparatus according to claim 100, further comprising a lower electrode arranged in said work table and a power supply for applying a high frequency potential to said lower electrode.

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111. (Previously Presented) The apparatus according to claim 100, wherein said apparatus is a plasma CVD apparatus to form a film on the process region of the substrate, the process gas being decomposable to provide a material of the film.

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112. (Previously Presented) The apparatus according to claim 100, wherein the process gas comprises first and second gases, and the first supply comprises first and second supply members respectively for supplying the first and second gases, and

wherein the second gas is transformable into the plasma when the first gas is excited and decomposed by said plasma.

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113. (Previously Presented) The apparatus according to claim 112, wherein said first supply member includes a supply port arranged between said window and said table, and said second supply member includes a supply port arranged between said window and said supply port of said first supply member.

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114. (Previously Presented) The apparatus according to claim 113, wherein said first supply member comprises a first supply head arranged between said window and said table and made of dielectric, and said supply port of said first supply member comprises a plurality of supply holes formed on said first supply member and arranged to uniformly cover the whole of the process region of the substrate mounted on said table.

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115. (Previously Presented) The apparatus according to claim 114, wherein said first supply head comprises a lattice formed of a combination of pipe elements through which the first gas flows.

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116. (Previously Presented) The apparatus according to claim 115, wherein said second supply member comprises a second supply head arranged between said window and said first supply head, made of dielectric, and comprising a continuous

frame formed of a combination of pipe elements through which the second gas flows,
and said supply port of said second supply member comprises a plurality of supply
holes formed on said second supply member.

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75 117. (Previously Presented) The apparatus according to claim 100, wherein
said dielectric window has a thickness in a preselected range.

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118. (Previously Presented) The apparatus according to claim 100, wherein
the pressure difference is controlled at a value that is lower than atmospheric pressure.

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119. (Previously Presented) The apparatus according to claims 85 or 100,
wherein said window has a thickness of approximately 30 mm to approximately 50 mm.

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127. (Previously Amended) An apparatus for processing a process region of a
substrate, using a plasma, comprising:

a container substantially formed of a conductive material;
a partition plate supported by said container and defining an air-tight process
container portion and an air-tight auxiliary container portion, and having a window plate
made of dielectric;

an exhaust pump for exhausting and setting at least one of said container portions to a vacuum;

a work table arranged in said process container portion and having a support face facing said window plate, the substrate being mountable on said support face with the process region facing said window plate;

a main supply for supplying a process gas between said window plate and the substrate mounted on said support face, at least part of the process gas being transformable into the plasma;

a planar spiral coil for generating an electromagnetic field between said window plate and the substrate mounted on said support face to induce generation of the plasma, arranged in said auxiliary container portion and facing said window plate;

a power supply section for applying a high frequency voltage to said planar spiral coil;

a pressure controller connected to said exhaust pump for keeping a pressure difference between pressures in said process and auxiliary container portions at a minimum value;

an auxiliary supply for supplying an inactive gas into said auxiliary container portion; and

a seat arranged on said window plate and supporting said planar spiral coil; wherein a passage through which coolant is circulated is formed in said seat.

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138. (Previously Amended) An apparatus for processing with a plasma a process region of a substrate, comprising:

a container;

a dielectric window supported by said container and defining a first container portion and a second container portion separated by said dielectric window;

a table for supporting the substrate in said first container portion to face said window;

an exhaust means connected to at least one of said container portions for drawing a vacuum;

a first supply for supplying a process gas to said first container portion;

a planar spiral coil for generating an electromagnetic field between said window and the substrate supported on said table to induce generation of the plasma, said planar spiral coil being provided in said second container portion proximate said window;

a power supply for supplying a voltage to said planar spiral coil; and

a second supply connected to said second container portion, comprising a gas source and a gas supply pipe for supplying an auxiliary gas to said second container portion;

wherein said exhaust means is controllable to control a pressure differential across said window at a minimum value.

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139. (Previously Presented) The apparatus according to claim 138, further comprising a controller for controlling said exhaust means to control the pressure differential.

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140. (Previously Presented) The apparatus according to claim 138, wherein said exhaust means is controllable according to an amount of the auxiliary gas supplied by said second supply to control the pressure differential across said window at the at the minimum value.

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141. (Previously Presented) The apparatus according to claim 138, wherein said exhaust means includes an exhaust pump controllable to control the pressure differential across said window at the minimum value.

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142. (Previously Presented) The apparatus according to claim 141, further comprising a controller for controlling said exhaust pump.

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143. (Previously Presented) The apparatus according to claim 138, further comprising a controller for controlling said exhaust means according to the supply of the auxiliary gas through said second supply, to control the pressure differential across said window at the minimum value.

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144. (Previously Presented) The apparatus according to claim 138, wherein said exhaust means is controllable according to a pressure in said first container portion.

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145. (Previously Presented) The apparatus according to claim 138, wherein said exhaust means includes an exhaust pump.

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146. (Previously Presented) The apparatus according to claim 145, further comprising a controller connected to said exhaust pump.

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147. (Previously Presented) The apparatus according to claim 138, wherein said container is substantially formed of a conductive material.

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148. (Previously Presented) The apparatus according to claim 138, wherein said dielectric window is supported on an inner surface of said container.

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149. (Previously Presented) The apparatus according to claim 138, further comprising grounding means for grounding said container.

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150. (Previously Amended) The apparatus according to claim 138, further comprising a cooler for cooling said planar spiral coil.

91 78
151. (Previously Amended) The apparatus according to claim 138, wherein
said auxiliary gas is a coolant by which said planar spiral coil is cooled.

92 78
152. (Previously Amended) The apparatus according to claim 138, wherein
said second supply comprises a shower head arranged above said planar spiral coil
and having a plurality of gas supply holes facing said planar spiral coil.

93 78
153. (Previously Amended) The apparatus according to claim 138, further
comprising a seat arranged on said window and supporting said planar spiral coil.

94 78
154. (Previously Presented) The apparatus according to claim 153, wherein a
passage through which a coolant is circulated is formed on said seat.

95 78
155. (Previously Amended) The apparatus according to claim 138, further
comprising a lower electrode arranged in said table and a power supply for applying a
high frequency potential to said lower electrode.

96 78
156. (Previously Presented) The apparatus according to claim 138, wherein
said apparatus is a plasma CVD apparatus to form a film on the process region of the
substrate, the process gas being decomposable to provide a material of the film.

157. (Previously Presented) The apparatus according to claim 138, wherein the process gas comprises first and second gases, and the first supply comprises first and second supply members respectively for supplying the first and second gases, and wherein the second gas is transformable into the plasma when the first gas is excited and decomposed by said plasma.

158. (Previously Presented) The apparatus according to claim 157, wherein said first supply member includes a supply port arranged between said window and said table, and said second supply member includes a supply port arranged between said window and said supply port of said first supply member.

159. (Previously Presented) The apparatus according to claim 158, wherein said first supply member comprises a first supply head arranged between said window and said table and made of dielectric, and said supply port of said first supply member comprises a plurality of supply holes formed on said first supply member and arranged to uniformly cover the whole of the process region of the substrate mounted on said table.

160. (Previously Presented) The apparatus according to claim 159, wherein said first supply head comprises a lattice formed of a combination of pipe elements through which the first gas flows.

101 100
161. (Previously Presented) The apparatus according to claim 160, wherein
said second supply member comprises a second supply head arranged between said
window and said first supply head, made of dielectric, and comprising a continuous
frame formed of a combination of pipe elements through which the second gas flows,
and said supply port of said second supply member comprises a plurality of supply
holes formed on said second supply member.

102 76
162. (Previously Presented) The apparatus according to claim 138, wherein
the pressure differential across said window is controlled to be in a preselected range.

103 76
163. (Previously Presented) The apparatus according to claim 138, wherein
said dielectric window has a thickness in a preselected range.

104 78
164. The apparatus according to claim 138, wherein said window has a
thickness of approximately 30 mm to approximately 50 mm.

165. (Previously Amended) An apparatus for processing a process region of a substrate, using a plasma, comprising:

a container substantially formed of a conductive material;

a partition plate supported by said container and defining an air-tight process container portion and an air-tight auxiliary container portion, and having a window plate made of dielectric;

a work table arranged in said process container portion and having a support face facing said window plate, the substrate being mountable on said support face with the process region facing said window plate;

a main supply for supplying a process gas between said window plate and the substrate mounted on said support face, at least part of the process gas being transformable into the plasma;

a planar spiral coil having a quadrilateral outer configuration for generating an electromagnetic field between said window plate and the substrate mounted on said support face to induce generation of the plasma, arranged in said auxiliary container portion and facing said window plate;

a power supply section for applying a high frequency voltage to said planar spiral coil;

a pressure controller controlling a pressure difference between a pressure in said process container portion and a pressure in said auxiliary container portion lower than a predetermined value;

a seat arranged on said window plate supporting said planar spiral coil, said seat having a passage therethrough for circulating a coolant; and

an exhaust pump connected to the auxiliary container portion and the process container portion.

167. (Previously Presented) An apparatus for processing a process region of a substrate, using a plasma, comprising:

a container substantially formed of a conductive material;

a partition plate supported by said container and defining an air-tight process container portion and an air-tight auxiliary container portion, and having a window plate made of dielectric;

an exhaust pump for exhausting and setting at least one of said container portions to a vacuum;

a work table arranged in said process container portion and having a support face facing said window plate, the substrate being mountable on said support face with the process region facing said window plate;

a main supply for supplying a process gas between said window plate and the substrate mounted on said support face, at least part of the process gas being transformable into the plasma;

a planar spiral coil for generating an electromagnetic field between said window plate and the substrate mounted on said support face to induce generation of the plasma, arranged in said auxiliary container portion and facing said window plate;

a power supply section for applying a high frequency voltage to said planar spiral coil;

a pressure controller connected to said exhaust pump for keeping a pressure difference between pressures in said process container portion and said auxiliary container portions at a minimum value; and

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a seat arranged on said window plate supporting said planar spiral coil, said seat
having a passage therethrough for circulating a coolant.